



## JX011N2 1A Sensitive SCR

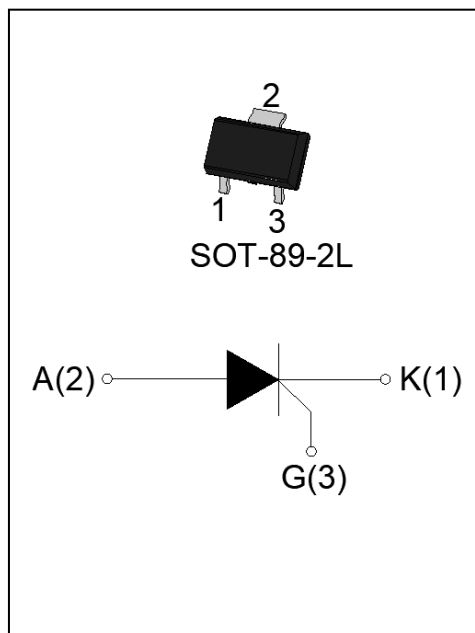
Rev.A.1.0

### DESCRIPTION:

The JX011N2 SCR provides high  $dV/dt$  rate with strong resistance to electromagnetic interface. It is especially recommended for use on residual current circuit breaker, straight hair, igniter etc. Package SOT-89-2L is RoHS compliant.

### MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
$V_{DRM} / V_{RRM}$	800	V
$I_{GT}$	$\leq 200$	$\mu A$



### ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	$^{\circ}C$
Operating junction temperature range	$T_j$	-40-125 <sup>①</sup>	$^{\circ}C$
Repetitive peak off-state voltage ( $T_j=25^{\circ}C$ )	$V_{DRM}$	800	V
Repetitive peak reverse voltage ( $T_j=25^{\circ}C$ )	$V_{RRM}$	800	V
Average on-state current ( $T_c \leq 72^{\circ}C$ )	$I_{T(AV)}$	0.6	A
RMS on-state current ( $T_c \leq 72^{\circ}C$ )	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current ( $t_p=10ms, T_j=25^{\circ}C$ )	$I_{TSM}$	12	A
Non repetitive surge peak on-state current ( $t_p=8.3ms, T_j=25^{\circ}C$ )		13	
$I^2t$ value for fusing ( $t_p=10ms, T_j=25^{\circ}C$ )	$I^2t$	0.72	$A^2s$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}, f=100Hz, T_j=125^{\circ}C$ )	$di/dt$	100	$A/\mu s$
Peak gate current ( $t_p=20\mu s, T_j=125^{\circ}C$ )	$I_{GM}$	1	A
Average gate power dissipation ( $T_j=125^{\circ}C$ )	$P_{G(AV)}$	0.1	W

Peak gate power	$P_{GM}$	2	W
Peak pulse voltage ( $T_j=25^\circ\text{C}$ ; non-repetitive, off-state; FIG.8)	$V_{pp}$	1	kV

**NOTE 1:** When we parallel connect a  $\leq 1\text{K}\Omega$  resistor between Gate and Cathode, the  $T_j$  can reach  $125^\circ\text{C}$ ; if without this resistor, the  $T_j$  only can reach  $110^\circ\text{C}$ .

### ELECTRICAL CHARACTERISTICS ( $T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
$I_{GT}$	$V_D=12\text{V } R_L=33\Omega$	-	40	200	$\mu\text{A}$
$V_{GT}$		-	0.6	0.8	V
$V_{GD}$	$V_D=V_{DRM} T_j=125^\circ\text{C}$	0.2	-	-	V
$I_L$	$I_G=1.2 I_{GT}$	-	-	5	mA
$I_H$	$I_T=0.05\text{A}$	-	-	4	mA
dV/dt	$V_D=540\text{V } T_j=125^\circ\text{C } R_{GK}=1\text{K}\Omega$	200	-	-	$\text{V}/\mu\text{s}$
	$V_D=540\text{V } T_j=125^\circ\text{C } R_{GK}=220\Omega$	500	-	-	
$t_{on}$	$I_G=10\text{mA } I_A=20\text{mA } I_R=2\text{mA}$	-	2	-	$\mu\text{s}$
$t_{off}$	$T_j=25^\circ\text{C}$	-	50	-	$\mu\text{s}$

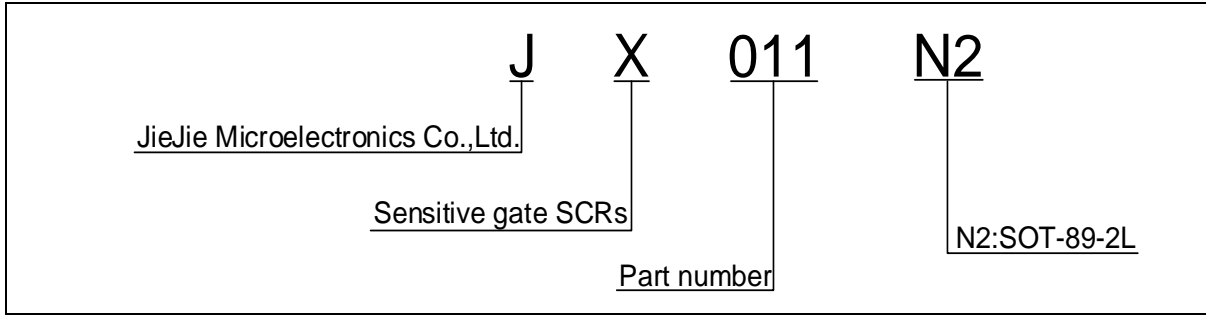
### STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_T=2\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.4	V
$V_{TO}$	Threshold voltage	$T_j=125^\circ\text{C}$	0.8	V
$R_D$	Dynamic Resistance	$T_j=125^\circ\text{C}$	0.1	$\Omega$
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	$\mu\text{A}$
$I_{RRM}$		$T_j=125^\circ\text{C}$	0.2	mA

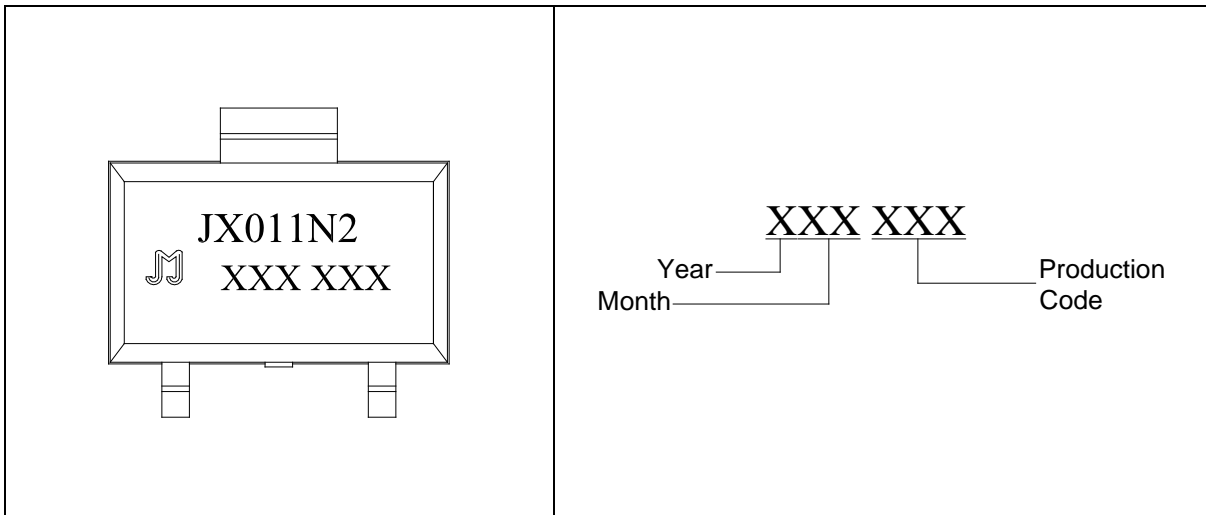
### THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	45	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (DC, in free air, $S=5\text{ cm}^2$ )	100	$^\circ\text{C}/\text{W}$

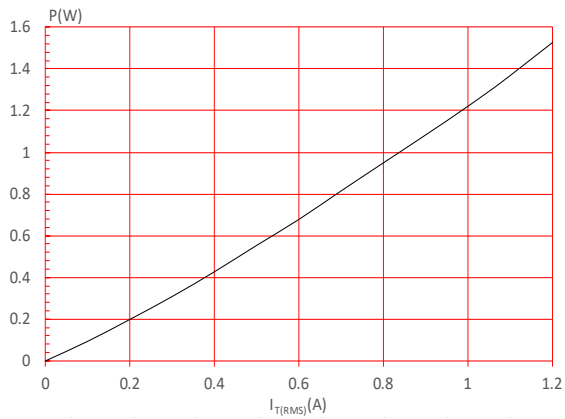
**ORDERING INFORMATION**



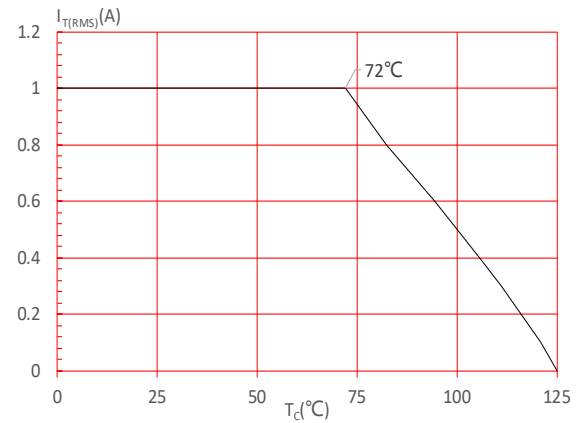
**MARKING**



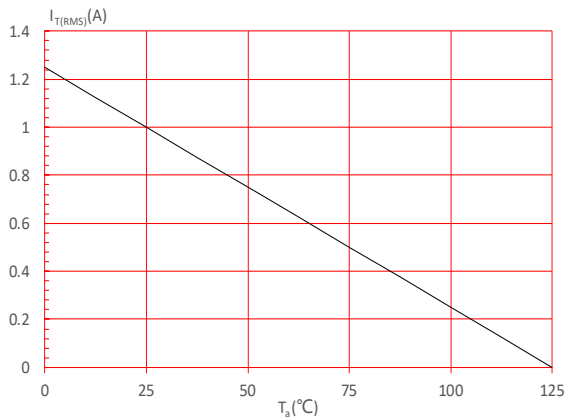
**FIG.1** Maximum power dissipation versus RMS on-state current



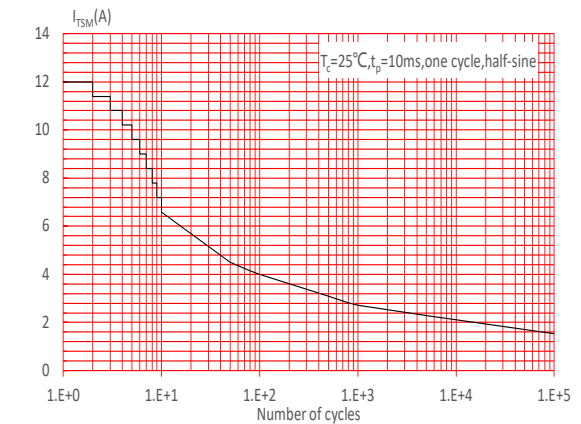
**FIG.2:** RMS on-state current versus case temperature



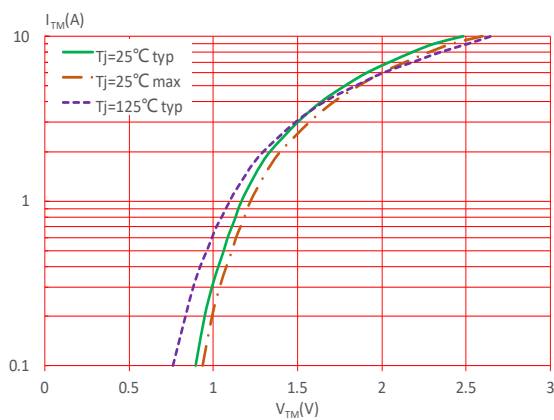
**FIG.3:** RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35μm)(full cycle)



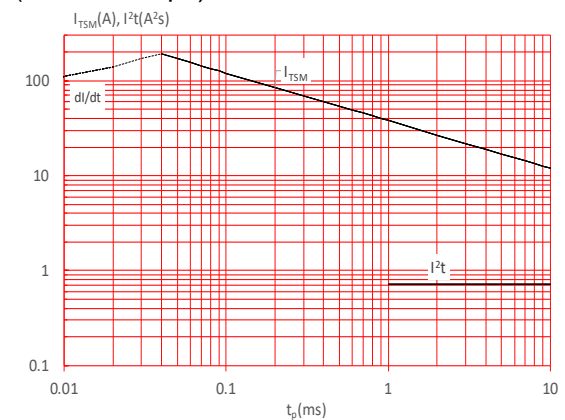
**FIG.4:** Surge peak on-state current versus number of cycles



**FIG.5:** On-state characteristics



**FIG.6:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 100\text{A}/\mu\text{s}$ )



**FIG.7:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

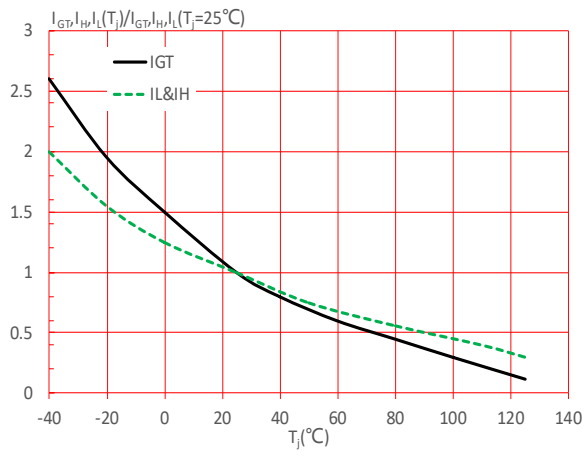
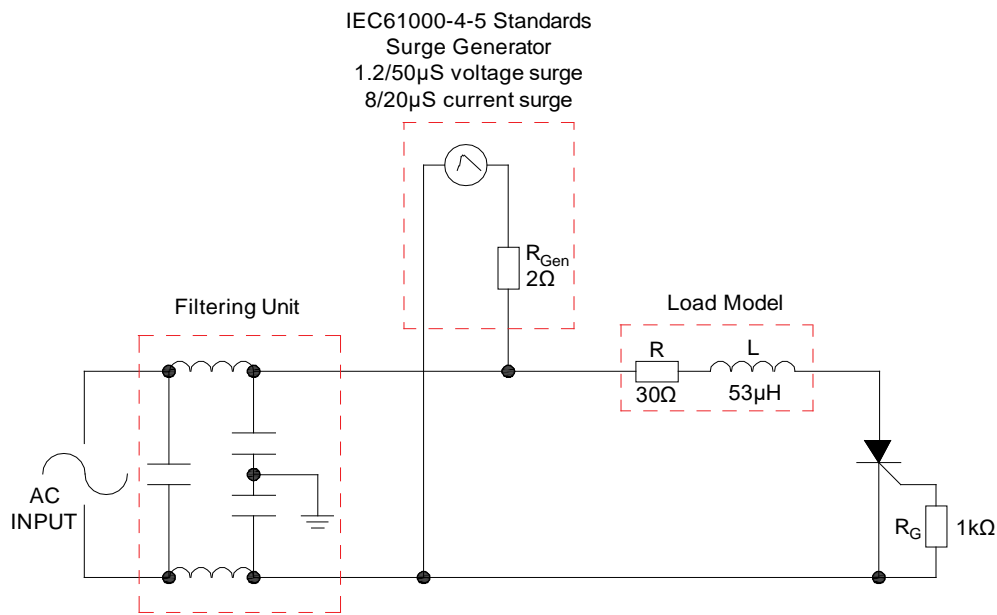
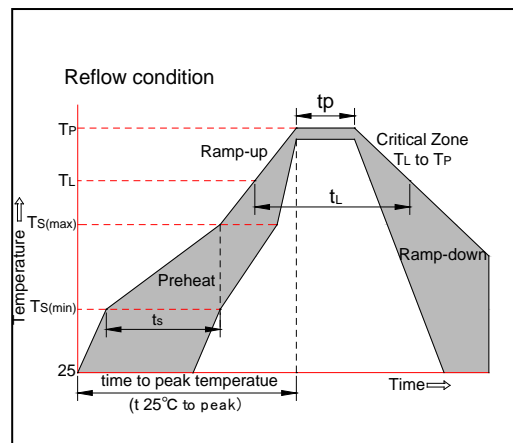


FIG.8: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



**SOLDERING PARAMETERS**

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ( $T_{s(min)}$ )	+150°C
	-Temperature Max ( $T_{s(max)}$ )	+200°C
	-Time (Min to Max) ( $t_s$ )	60-180 secs.
Average ramp up rate (Liquidus Temp ( $T_L$ ) to peak)		3°C/sec. Max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature( $T_L$ ) (Liquidus)	+217°C
	-Temperature( $t_L$ )	60-150 secs.
Peak Temp ( $T_p$ )		+260(+0/-5)°C
Time within 5°C of actual Peak Temp ( $t_p$ )		20-40secs.
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp ( $T_p$ )		8 min. Max
Do not exceed		+260°C



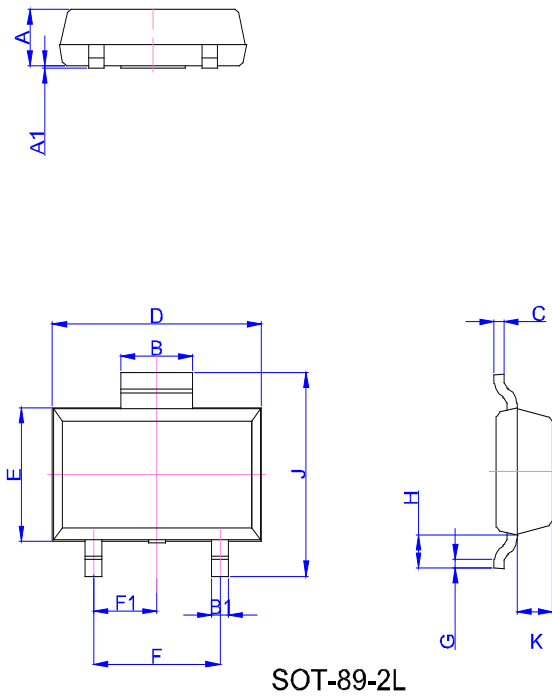
**ORDERING INFORMATION**

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT( $\mu$ A)	Package	Base qty. (pcs)	Delivery mode
JX011N2	800	$\leq 200$	SOT-89-2L	4,000	Tape & Reel

**Document Revision History**

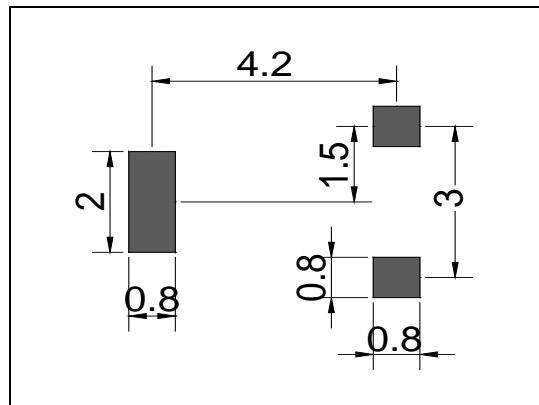
Date	Revision	Changes
Apr.12, 2023	A.1.0	Last update

**PACKAGE MECHANICAL DATA**



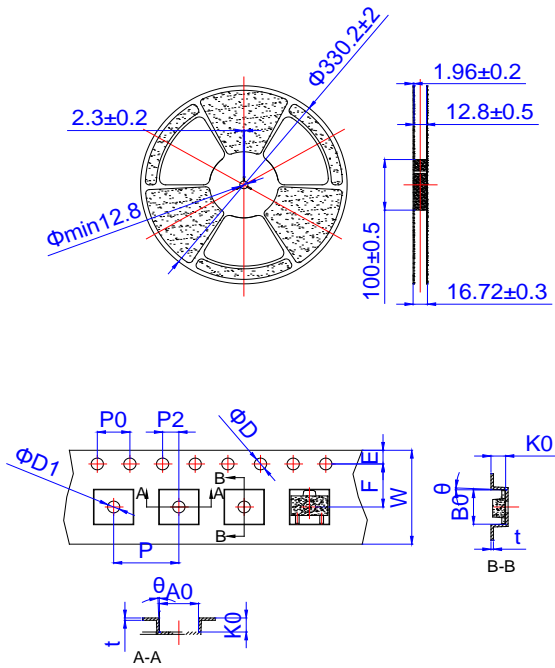
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.3	1.4	1.5	0.051	0.055	0.059
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	1.6	1.7	1.8	0.063	0.067	0.071
B1	0.3	0.4	0.5	0.012	0.016	0.020
C	0.22	0.254	0.32	0.009	0.010	0.013
D	4.75	4.95	5.15	0.187	0.195	0.203
E	2.90		3.30	0.114		0.130
F	2.80		3.20	0.110		0.126
F1	1.40		1.60	0.055		0.063
G	0.20	0.30	0.40	0.008	0.012	0.016
H	0.58	0.78	0.98	0.023	0.031	0.039
J	4.30	4.50	4.70	0.169	0.177	0.185
K	0.80		1.00	0.031		0.039

**FOOTPRINT-SOT-89-2L (dimensions in mm)**






DELIVERY MODE



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
P2	1.90	2.00	2.10	0.075	0.079	0.082
D	-	1.50	1.60	-	0.059	0.063
D1	1.50	-	-	0.059	-	-
P0	3.90	4.00	4.10	0.154	0.157	0.161
10P0	39.80	40.00	40.20	1.567	1.575	1.583
W	-	-	12.30	-	-	0.482
P	7.90	8.00	8.10	0.311	0.315	0.319
A0	5.20	5.30	5.40	0.204	0.208	0.212
B0	4.80	4.90	5.00	0.188	0.192	0.196
K0	1.75	1.85	1.95	0.069	0.073	0.076
t	0.20	0.25	0.30	0.008	0.010	0.012
$\theta$	3°		5°	3°		5°

PACKAGE	OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
SOT-89-2L	TAPING	4,000	40,000	13 inch

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